



μ A78S40 Universal Switching Regulator Subsystem

Linear Division Voltage Regulators

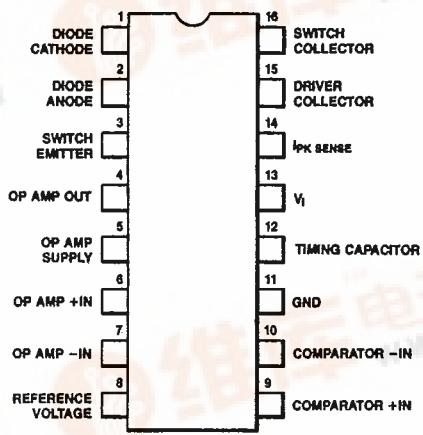
Description

The μ A78S40 is a monolithic regulator subsystem consisting of all the active building blocks necessary for switching regulator systems. The device consists of a temperature compensated voltage reference, a duty-cycle controllable oscillator with an active current limit circuit, an error amplifier, high current, high voltage output switch, a power diode and an uncommitted operational amplifier. The device can drive external NPN or PNP transistors when currents in excess of 1.5 A or voltages in excess of 40 V are required. The device can be used for step-down, step-up or inverting switching regulators as well as for series pass regulators. It features wide supply voltage range, low standby power dissipation, high efficiency and low drift. It is useful for any stand-alone, low part count switching system and works extremely well in battery operated systems.

- Step-Up, Step-Down or Inverting Switching Regulators
- Output Adjustable From 1.25 V to 40 V
- Peak Currents To 1.5 A Without External Transistors
- Operation From 2.5 V to 40 V Input
- Low Standby Current Drain
- 80 dB Line And Load Regulation
- High Gain, High Current, Independent OP AMP
- Pulse Width Modulation With No Double Pulsing

Connection Diagram

16-Lead DIP (Top View)



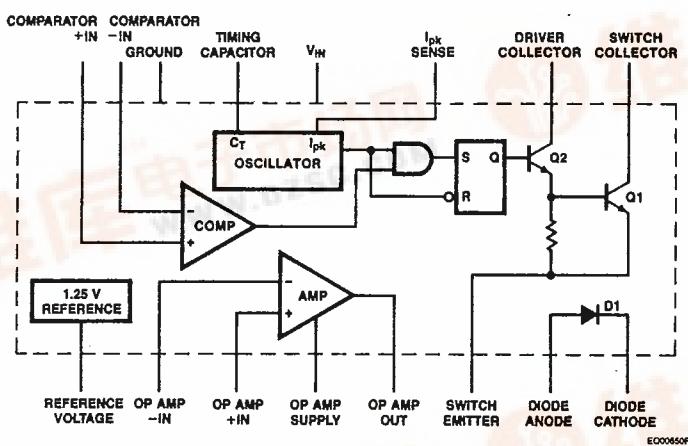
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Order Information

Device Code	Package Code	Package Description
μ A78S40DM	7B	Ceramic DIP
μ A78S40PV	9B	Molded DIP
μ A78S40DC	7B	Ceramic DIP
μ A78S40PC	9B	Molded DIP

Block Diagram



μ A78S40

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Absolute Maximum Ratings

Storage Temperature Range	
Ceramic DIP	-65°C to +175°C
Molded DIP	-65°C to +150°C
Operating Temperature Range	
Extended (μ A78S40M)	-55°C to +125°C
Industrial (μ A78S40V)	-40°C to +125°C
Commercial (μ A78S40C)	0°C to +70°C
Lead Temperature	
Ceramic DIP (soldering, 60 s)	300°C
Molded DIP (soldering, 10 s)	265°C
Internal Power Dissipation ^{1,2}	
16L-Ceramic DIP	1.50 W
16L-Molded DIP	1.04 W
Input Voltage from V+ to V-	40 V
Input Voltage from V+ Op Amp to V- Op Amp	40 V

Notes

1. T_J Max = 150°C for the Molded DIP, and 175°C for the Ceramic DIP.
2. Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 16L-Ceramic DIP at 10 mW/°C, and the 16L-Molded DIP at 8.3 mW/°C.
3. For supply voltages less than 30 V, the absolute maximum voltage is equal to the supply voltage.

Functional Description

The μ A78S40 is a variable frequency, variable duty cycle device. The initial switching frequency is set by the timing capacitor.¹ The initial duty cycle is 6:1. This switching frequency and duty cycle can be modified by two mechanisms — the current limit circuitry (I_{pk} sense) and the comparator.

The comparator modifies the OFF time. When the output voltage is correct, the comparator output is in the HIGH state and has no effect on the circuit operation. If the output voltage is too high then the comparator output goes LOW. In the LOW state the comparator inhibits the turn-on of the output stage switching transistors. As long as the comparator is LOW the system is in OFF time. As the output current rises the OFF time decreases. As the output current nears its maximum the OFF time approaches its minimum value. The comparator can inhibit several ON cycles, one ON cycle or any portion of an ON cycle. Once the ON cycle has begun the comparator cannot inhibit until the beginning of the next ON cycle.

The current limit modifies the ON time. The current limit is activated when a 300 mV potential appears between lead 13 (V_{cc}) and lead 14 (I_{pk}). This potential is intended to result when designed for peak current flows through R_{sc}. When the peak current is reached the current limit is turned on. The current limit circuitry provides for a quick end to ON time and the immediate start of OFF time.

Note

1. Oscillator frequency is set by a single external capacitor and may be varied over a range of 100 Hz to 100 kHz.

Common Mode Input Range (Error Amplifier and Op Amp)	-0.3 to V+
Differential Input Voltage ³	±30 V
Output Short Circuit Duration (Op Amp)	Indefinite
Current from V _{REF}	10 mA
Voltage from Switch Collectors to GND	40 V
Voltage from Switch Emitters to GND	40 V
Voltage from Switch Collectors to Emitter	40 V
Voltage from Power Diode to GND	40 V
Reverse Power Diode Voltage	40 V
Current through Power Switch	1.5 A
Current through Power Diode	1.5 A

Generally the oscillator is free running but the current limit action tends to reset the timing cycle.

Increasing load results in more current limited ON time and less OFF time. The switching frequency increases with load current.

V_{FD} is the forward voltage drop across the internal power diode. It is listed on the data sheet as 1.25 V typical, 1.5 V maximum. If an external diode is used, then its own forward voltage drop must be used for V_{FD} .

V_{SAT} is the voltage across the switch element (output transistors Q1 and Q2) when the switch is closed or ON. This is listed on the data sheet as output saturation voltage.

Output saturation voltage 1 — defined as the switching element voltage for Q2 and Q1 in the Darlington configuration with collectors tied together. This applies to Figure 1, the step down mode.

Output saturation voltage 2 — switching element voltage for Q1 only when used as a transistor switch. This applies to Figure 2, the step up mode.

For the inverting mode, Figure 3, the saturation voltage of the external transistor should be used for V_{SAT} .

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Electrical Characteristics T_A = Operating temperature range, V_I = 5.0 V, $V_{Op\ Amp}$ = 5.0 V, unless otherwise specified.

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
General Characteristics						
I_{CC}	Supply Current (Op Amp Disconnected)	V_I = 5.0 V		1.8	3.5	mA
		V_I = 40 V		2.3	5.0	mA
I_{CC}	Supply Current (Op Amp Connected)	V_I = 5.0 V			4.0	mA
		V_I = 40 V			5.5	mA
Reference Section						
V_{REF}	Reference Voltage ¹	I_{REF} = 1.0 mA	Extend $-55^{\circ}\text{C} < T_A < +125^{\circ}\text{C}$, Comm $0 < T_A < +70^{\circ}\text{C}$, Indus $-40^{\circ}\text{C} < T_A < +85^{\circ}\text{C}$	1.180	1.245	1.310
V_R LINE	Reference Voltage Line Regulation	V_I = 3.0 V to V_I = 40 V, T_A = 25°C		0.04	0.2	mV/V
V_R LOAD	Reference Voltage Load Regulation	I_{REF} = 1.0 mA to I_{REF} = 10 mA, T_A = 25°C		0.2	0.5	mV/mA
Oscillator Section						
I_{CHG}	Charging Current	V_I = 5.0 V, T_A = 25°C	20		50	μA
I_{CHG}	Charging Current	V_I = 40 V, T_A = 25°C	20		70	μA
I_{DISCHG}	Discharge Current	V_I = 5.0 V, T_A = 25°C	150		250	μA
I_{DISCHG}	Discharge Current	V_I = 40 V, T_A = 25°C	150		350	μA
V_{osc}	Oscillator Voltage Swing	V_I = 5.0 V, T_A = 25°C		0.5		V
t_{on}/t_{off}	Ratio of Charge/ Discharge Time			6.0		$\mu\text{s}/\mu\text{s}$
Current Limit Section						
V_{CLS}	Current Limit Sense Voltage	T_A = 25°C	250		350	mV
Output Switch Section						
$V_{SAT\ 1}$	Output Saturation Voltage 1	I_{SW} = 1.0 A, Figure 1		1.1	1.3	V
$V_{SAT\ 2}$	Output Saturation Voltage 2	I_{SW} = 1.0 A, Figure 2		0.45	0.7	V
h_{FE}	Output Transistor Current Gain	I_C = 1.0 A, V_{CE} = 5.0 V, T_A = 25°C		70		
I_L	Output Leakage Current	V_O = 40 V, T_A = 25°C		10		nA
Power Diode						
V_{FD}	Forward Voltage Drop	I_D = 1.0 A		1.25	1.5	V
I_{DR}	Diode Leakage Current	V_D = 40 V, T_A = 25°C		10		nA
Comparator						
V_{IO}	Input Offset Voltage	$V_{CM} = V_{REF}$		1.5	15	mV
I_{IB}	Input Bias Current	$V_{CM} = V_{REF}$		35	200	nA
I_{IO}	Input Offset Current	$V_{CM} = V_{REF}$		5.0	75	nA

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Electrical Characteristics T_A = Operating temperature range, $V_I = 5.0$ V, $V_{Op\ Amp} = 5.0$ V, unless otherwise specified.

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{CM}	Common Mode Voltage Range	$T_A = 25^\circ C$	0		$V_1 - 2$	V
PSRR	Power Supply Rejection Ratio	$V_I = 3.0$ V to 40 V, $T_A = 25^\circ C$	70	96		dB
Output Operational Amplifier						
V_{IO}	Input Offset Voltage	$V_{CM} = 2.5$ V		4.0	15	mV
I_{IB}	Input Bias Current	$V_{CM} = 2.5$ V		30	200	nA
I_{IO}	Input Offset Current	$V_{CM} = 2.5$ V		5.0	75	nA
A_{Vs+}	Voltage Gain +	$R_L = 2.0$ k Ω to GND; $V_O = 1.0$ V to 2.5 V, $T_A = 25^\circ C$	25	250		V/mV
A_{Vs-}	Voltage Gain -	$R_L = 2.0$ k Ω to V_+ (Op Amp) $V_O = 1.0$ V to 2.5 V, $T_A = 25^\circ C$	25	250		V/mV
V_{CM}	Common Mode Voltage Range	$T_A = 25^\circ C$	0		$V_{CC} - 2$	V
CMR	Common Mode Rejection	$V_{CM} = 0$ V to 3.0 V, $T_A = 25^\circ C$	76	100		dB
PSRR	Power Supply Rejection Ratio	V_+ Op Amp = 3.0 to 40 V, $T_A = 25^\circ C$	76	100		dB
I_{O+}	Output Source Current	$T_A = 25^\circ C$	75	150		mA
I_{O-}	Output Sink Current	$T_A = 25^\circ C$	10	35		mA
SR	Slew Rate	$T_A = 25^\circ C$		0.6		V/ μ s
V_{OL}	Output Voltage LOW	$I_L = -5.0$ mA, $T_A = 25^\circ C$			1.0	V
V_{OH}	Output Voltage HIGH	$I_L = 50$ mA, $T_A = 25^\circ C$	$V + OP\ Amp$ -3.0 V			V

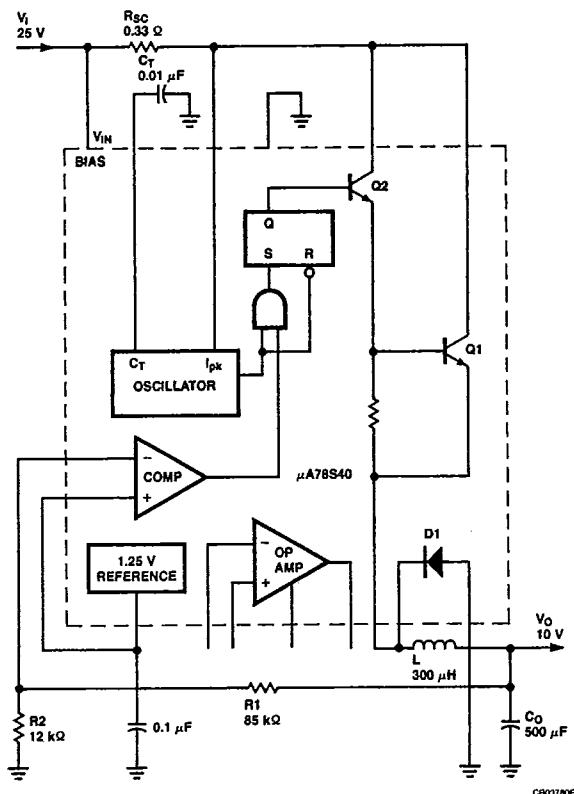
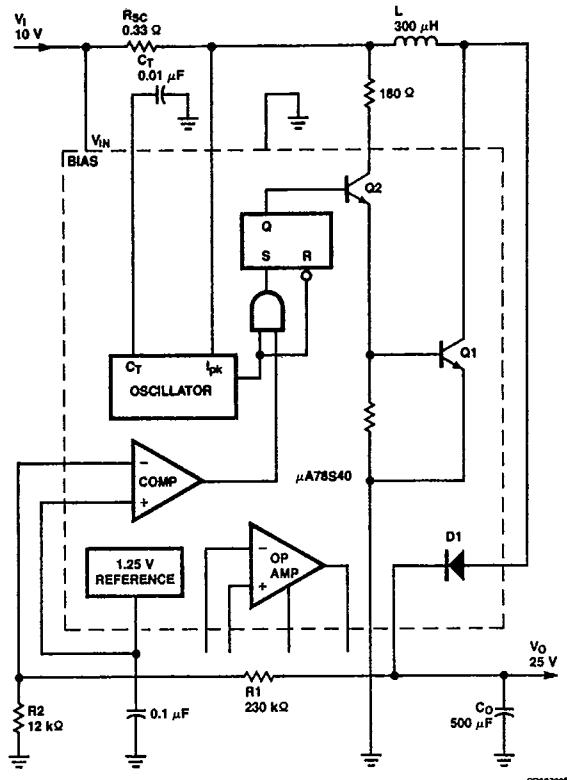
Note

1. Selected devices with tightened tolerance reference voltage available.

Design Formulas

CHARACTERISTIC	STEP-DOWN	STEP-UP	INVERTING	UNIT
$\frac{t_{on}}{t_{off}}$	$\frac{V_O + V_D}{V_I - V_{SAT} - V_O}$	$\frac{V_O + V_D - V_I}{V_I - V_{SAT}}$	$\frac{ V_O + V_D}{V_I - V_{SAT}}$	
$(t_{on} + t_{off}) \text{ Max}$	$\frac{1}{f_{\text{Min}}}$	$\frac{1}{f_{\text{Min}}}$	$\frac{1}{f_{\text{Min}}}$	μs 6
C_T	$4 \times 10^{-5} t_{on}$	$4 \times 10^{-5} t_{on}$	$4 \times 10^{-5} t_{on}$	μF
I_{pk}	$2 I_O \text{ Max}$	$2 I_O \text{ Max} \cdot \frac{t_{on} + t_{off}}{t_{off}}$	$2 I_O \text{ Max} \cdot \frac{t_{on} + t_{off}}{t_{off}}$	A
L_{Min}	$\left(\frac{V_I - V_{SAT} - V_O}{I_{pk}} \right) t_{on} \text{ Max}$	$\left(\frac{V_I - V_{SAT}}{I_{pk}} \right) t_{on} \text{ Max}$	$\left(\frac{V_I - V_{SAT}}{I_{pk}} \right) t_{on} \text{ Max}$	μH
R_{SC}	$0.33/I_{pk}$	$0.33/I_{pk}$	$0.33/I_{pk}$	Ω
C_O	$\frac{I_{pk} (t_{on} + t_{off})}{8 V_{\text{ripple}}}$	$\approx \frac{I_O}{V_{\text{ripple}}} \cdot t_{on}$	$\approx \frac{I_O}{V_{\text{ripple}}} \cdot t_{on}$	μF

Note V_{SAT} = Saturation voltage of the switching element V_D = Forward voltage of the flyback diode

Figure 1 Typical Step-Down Operational Performance ($T_A = 25^\circ\text{C}$)Figure 2 Typical Step-Up Operational Performance ($T_A = 25^\circ\text{C}$)

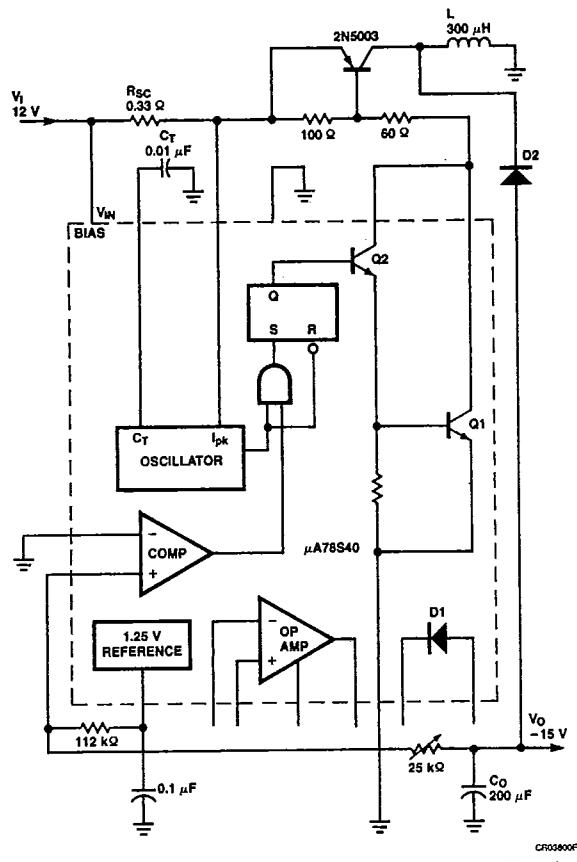
Characteristic	Condition	Typical Value
Output Voltage	$I_O = 200 \text{ mA}$	10 V
Line Regulation	$20 \leq V_1 \leq 30 \text{ V}$	1.5 mV
Load Regulation	$5.0 \text{ mA} \leq I_O$	
	$I_O \leq 300 \text{ mA}$	3.0 mV
Max Output Current	$V_O = 9.5 \text{ V}$	500 mA
Output Ripple	$I_O = 200 \text{ mA}$	50 mV
Efficiency	$I_O = 200 \text{ mA}$	74%
Standby Current	$I_O = 200 \text{ mA}$	2.8 mA

Notes

1. For $I_O \geq 200 \text{ mA}$ use external diode to limit on-chip power dissipation.
2. It is recommended that the internal reference (lead 8) be bypassed by a $0.1 \mu\text{F}$ capacitor directly to (lead 11) the ground point of the μA78S40.

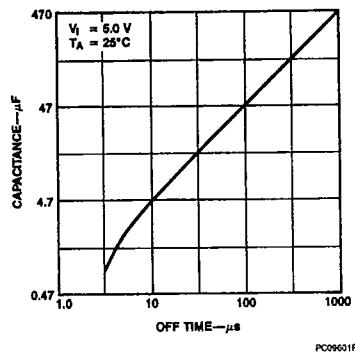
Characteristic	Condition	Typical Value
Output Voltage	$I_O = 50 \text{ mA}$	25 V
Line Regulation	$5.0 \text{ V} \leq V_1 \leq 15 \text{ V}$	4.0 mV
Load Regulation	$5.0 \text{ mA} \leq I_O$	
	$I_O \leq 100 \text{ mA}$	2.0 mV
Max Output Current	$V_O = 23.75 \text{ V}$	160 mA
Output Ripple	$I_O = 50 \text{ mA}$	30 mV
Efficiency	$I_O = 50 \text{ mA}$	79%
Standby Current	$I_O = 50 \text{ mA}$	2.6 mA

Figure 3 Typical Inversion Operational Performance
($T_A = 25^\circ\text{C}$)



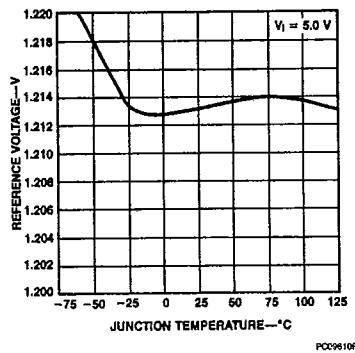
Typical Performance Curves

Capacitance vs OFF Time

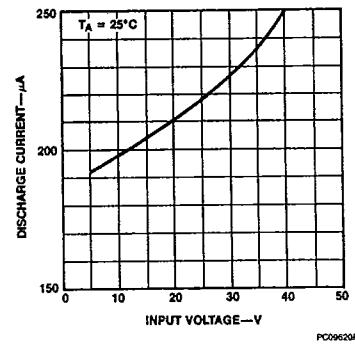


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Reference Voltage vs Junction Temperature



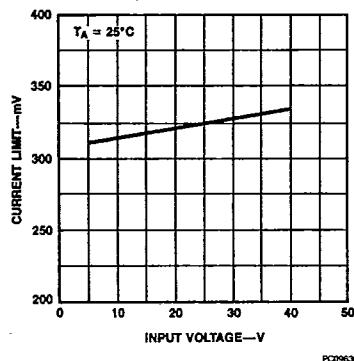
Discharge Current vs Input Voltage



Characteristic	Condition	Typical Value
Output Voltage	$I_O = 100 \text{ mA}$	-15 V
Line Regulation	$8.0 \text{ V} \leq V_I < 18 \text{ V}$	5.0 mV
Load Regulation	$5.0 \text{ mA} \leq I_O$	
	$I_O \leq 150 \text{ mA}$	3.0 mV
Max Output Current	$V_O = 14.25 \text{ V}$	160 mA
Output Ripple	$I_O = 100 \text{ mA}$	20 mV
Efficiency	$I_O = 100 \text{ mA}$	70%
Standby Current	$I_O = 100 \text{ mA}$	2.3 mA

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Typical Performance Curves (Cont.)**Current Limit Sense Voltage vs
Input Voltage****Typical Pulse Width Modulator Application**